

- **V<sub>CC</sub> Current (Commercial/Industrial)**
  - Operating: 10mA/12mA
  - CMOS Standby: 10µA/10µA
- **Access Times**
  - 55/70 (Commercial or Industrial)
- **Single 3.3 Volts ± 0.3V Power Supply**
- **Easy Memory Expansion Using  $\overline{CE}_1$ ,  $CE_2$  and  $\overline{OE}$  Inputs**
- **Common Data I/O**
- **Three-State Outputs**
- **Fully TTL Compatible Inputs and Outputs**
- **Advanced CMOS Technology**
- **Automatic Power Down**
- **Packages**
  - 32-Pin 445 mil SOP
  - 32-Pin TSOP

### DESCRIPTION

The P3C1024L is a 1,048,576-bit low power CMOS static RAM organized as 128Kx8. The CMOS memory requires no clocks or refreshing, and has equal access and cycle times. Inputs are fully TTL-compatible. The RAM operates from a single 3.3V ± 0.3V tolerance power supply.

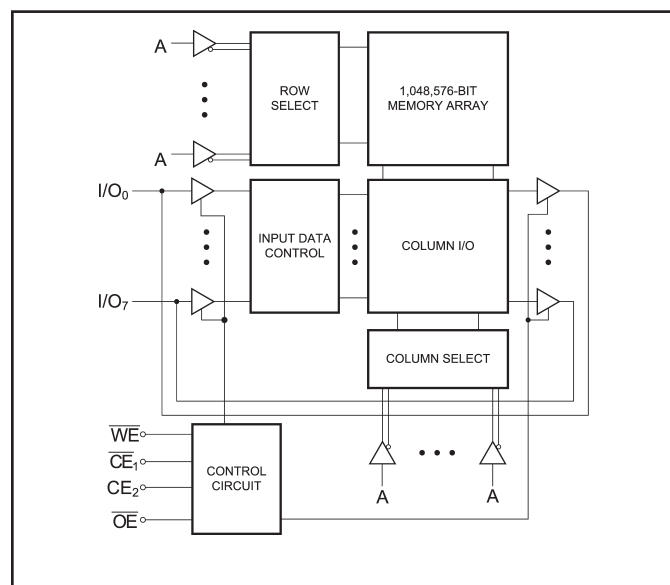
Access times of 55 ns and 70 ns are available. CMOS is utilized to reduce power consumption to a low level.

The P3C1024L device provides asynchronous operation with matching access and cycle times. Memory

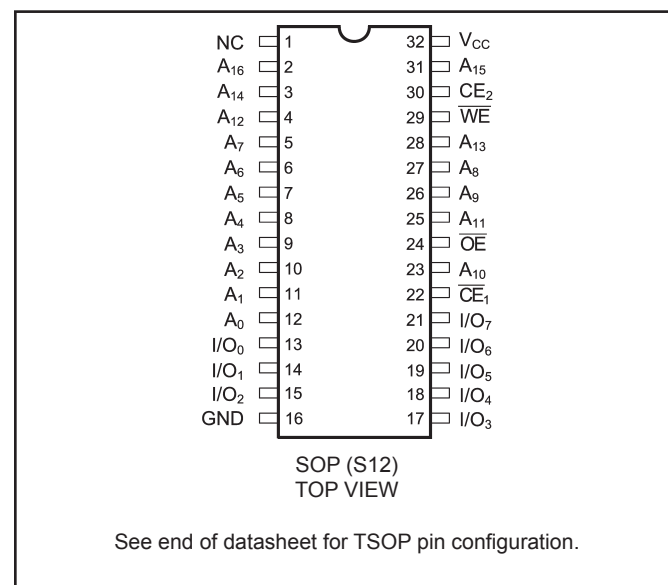
locations are specified on address pins  $A_0$  to  $A_{16}$ . Reading is accomplished by device selection ( $\overline{CE}_1$  low and  $CE_2$  high) and output enabling ( $\overline{OE}$ ) while write enable ( $\overline{WE}$ ) remains HIGH. By presenting the address under these conditions, the data in the addressed memory location is presented on the data input/output pins. The input/output pins stay in the HIGH Z state when either  $\overline{CE}_1$  or  $\overline{OE}$  is HIGH or  $\overline{WE}$  or  $CE_2$  is LOW.

The P3C1024L is packaged in a 32-pin TSOP and 445 mil SOP.

### FUNCTIONAL BLOCK DIAGRAM



### PIN CONFIGURATION





## RECOMMENDED OPERATING TEMPERATURE & SUPPLY VOLTAGE

Temperature Range (Ambient)	Supply Voltage
Commercial (0°C to 70°C)	$3.0V \leq V_{CC} \leq 3.6V$
Industrial (-40°C to 85°C)	

## MAXIMUM RATINGS<sup>(1)</sup>

Stresses greater than those listed can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this data sheet. Exposure to Maximum Ratings for extended periods can adversely affect device reliability.

Sym	Parameter	Min	Max	Unit
$V_{CC}$	Supply Voltage with Respect to GND	-0.3	3.9	V
$V_{TERM}$	Terminal Voltage with Respect to GND	-0.3	$V_{CC} + 0.3$	V
$T_A$	Operating Ambient Temperature	-55	125	°C
$S_{TG}$	Storage Temperature	-65	150	°C
$I_{OUT}$	Output Current into Low Outputs		20	mA
$I_{LAT}$	Latch-up Current	> 200		mA

## DC ELECTRICAL CHARACTERISTICS

(Over Recommended Operating Temperature & Supply Voltage)<sup>(2)</sup>

Sym	Parameter	Test Conditions	Min	Max	Unit	
$V_{OH}$	Output High Voltage ( $I/O_0 - I/O_7$ )	$I_{OH} = -1mA, V_{CC} = 3.0V$	2.4		V	
$V_{OL}$	Output Low Voltage ( $I/O_0 - I/O_7$ )	$I_{OL} = 2.1mA, V_{CC} = 3.0V$		0.4	V	
$V_{IH}$	Input High Voltage		2.2	$V_{CC} + 0.3$	V	
$V_{IL}$	Input Low Voltage		-0.3	0.8	V	
$I_{LI}$	Input Leakage Current	$GND \leq V_{IN} \leq V_{CC}$	IND	-2	+2	$\mu A$
			COM	-1	+1	
$I_{LO}$	Output Leakage Current	$GND \leq V_{OUT} \leq V_{CC},$ $\overline{CE}_1 \geq V_{IH} \text{ or } CE_2 \leq V_{IL}$	IND	-2	+2	$\mu A$
			COM	-1	+1	
$I_{SB}$	$V_{CC}$ Current TTL Standby Current (TTL Input Levels)	$V_{CC} = 3.6V, I_{OUT} = 0 \text{ mA}$ $\overline{CE}_1 = V_{IH} \text{ or } CE_2 = V_{IL}$		3	mA	
$I_{SB1}$	$V_{CC}$ Current CMOS Standby Current (CMOS Input Levels)	$V_{CC} = 3.6V, I_{OUT} = 0 \text{ mA}$ $\overline{CE}_1 \geq V_{CC} - 0.2V, CE_2 \leq 0.2V$		10	$\mu A$	

**CAPACITANCES<sup>(4)</sup>** $(V_{CC} = 5.0V, T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$ 

Symbol	Parameter	Test Conditions	Max	Unit
$C_{IN}$	Input Capacitance	$V_{IN}=0V$	8	pF
$C_{OUT}$	Output Capacitance	$V_{OUT}=0V$	9	pF

**POWER DISSIPATION CHARACTERISTICS VS. SPEED**

Symbol	Parameter	Temperature Range	-55	-70	Unit
$I_{CC}$	Dynamic Operating Current	Commercial	10	8	mA
		Industrial	12	10	mA

\*Tested with outputs open and all address and data inputs changing at the maximum write-cycle rate.

The device is continuously enabled for writing, i.e.,  $CE_2 \geq V_{IH}$  (min),  $\overline{CE}_1$  and  $\overline{WE} \leq V_{IL}$  (max),  $\overline{OE}$  is high. Switching inputs are 0V and 3V.

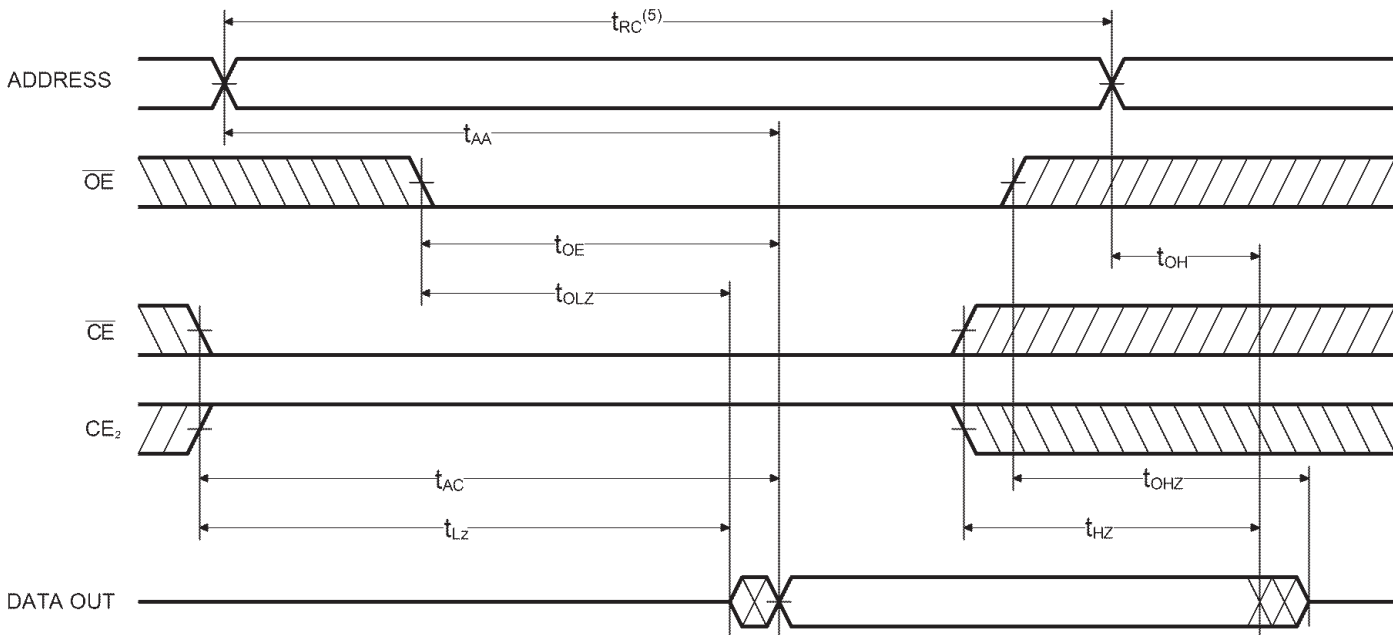
**AC ELECTRICAL CHARACTERISTICS - READ CYCLE**

(Over Recommended Operating Temperature & Supply Voltage)

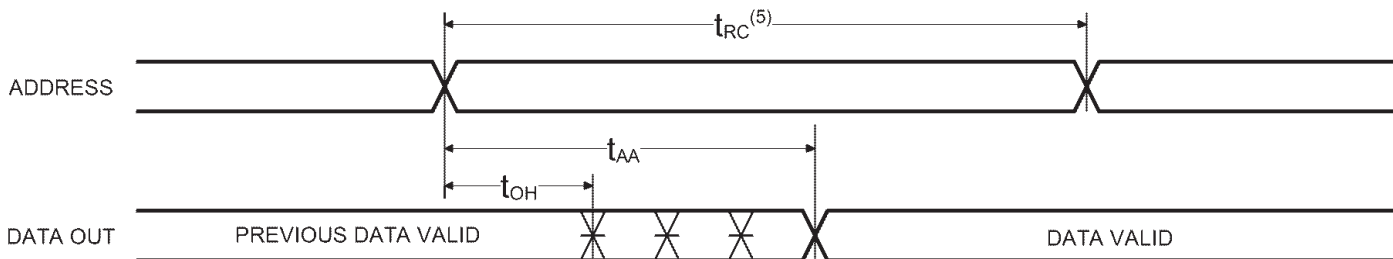
Symbol	Parameter	-55		-70		Unit
		Min	Max	Min	Max	
$t_{RC}$	Read Cycle Time	55		70		ns
$t_{AA}$	Address Access Time		55		70	ns
$t_{AC}$	Chip Enable Access Time		55		70	ns
$t_{OH}$	Output Hold from Address Change	10		10		ns
$t_{LZ}$	Chip Enable to Output in Low Z	10		10		ns
$t_{HZ}$	Chip Disable to Output in High Z		20		25	ns
$t_{OE}$	Output Enable Low to Data Valid		25		35	ns
$t_{OLZ}$	Output Enable Low to Low Z	5		5		ns
$t_{OHZ}$	Output Enable High to High Z		20		25	ns
$t_{PU}$	Chip Enable to Power Up Time	0		0		ns
$t_{PD}$	Chip Disable to Power Down Time		55		70	ns



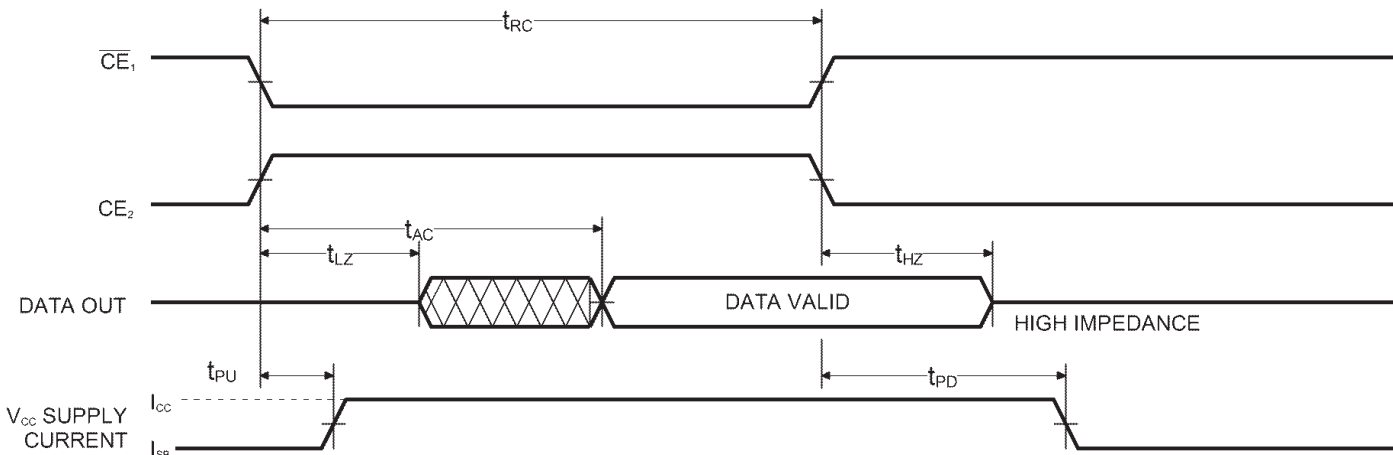
### READ CYCLE NO. 1 ( $\overline{OE}$ CONTROLLED)<sup>(1)</sup>



### READ CYCLE NO. 2 (ADDRESS CONTROLLED)



### READ CYCLE NO. 3 ( $\overline{CE}$ CONTROLLED)



**Notes:**

1.  $\overline{WE}$  is HIGH for READ cycle.
2.  $\overline{CE}_1$  and  $\overline{OE}$  is LOW, and  $CE_2$  is HIGH for READ cycle.
3. ADDRESS must be valid prior to, or coincident with later of  $\overline{CE}_1$  transition LOW or  $CE_2$  transition HIGH.
4. Transition is measured  $\pm 200$  mV from steady state voltage prior to change, with loading as specified in Figure 1. This parameter is sampled and not 100% tested.
5. READ Cycle Time is measured from the last valid address to the first transitioning address.

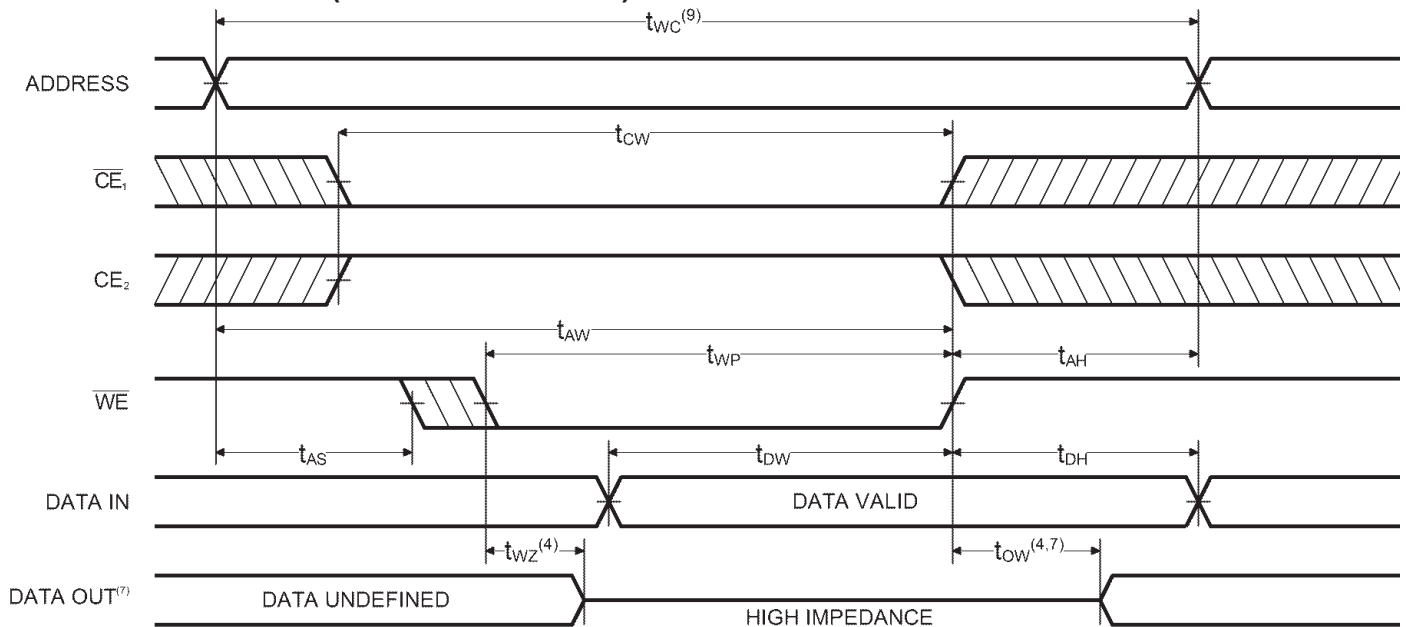


## AC CHARACTERISTICS - WRITE CYCLE

(Over Recommended Operating Temperature & Supply Voltage)

Symbol	Parameter	-55		-70		Unit
		Min	Max	Min	Max	
$t_{WC}$	Write Cycle Time	55		70		ns
$t_{CW}$	Chip Enable Time to End of Write	40		60		ns
$t_{AW}$	Address Valid to End of Write	40		60		ns
$t_{AS}$	Address Set-up Time	0		0		ns
$t_{WP}$	Write Pulse Width	40		50		ns
$t_{AH}$	Address Hold Time	0		0		ns
$t_{DW}$	Data Valid to End of Write	25		30		ns
$t_{DH}$	Data Hold Time	0		0		ns
$t_{WZ}$	Write Enable to Output in High Z		20		25	ns
$t_{OW}$	Output Active from End of Write	10		10		ns

### WRITE CYCLE NO. 1 ( $\overline{WE}$ CONTROLLED)<sup>(6)</sup>

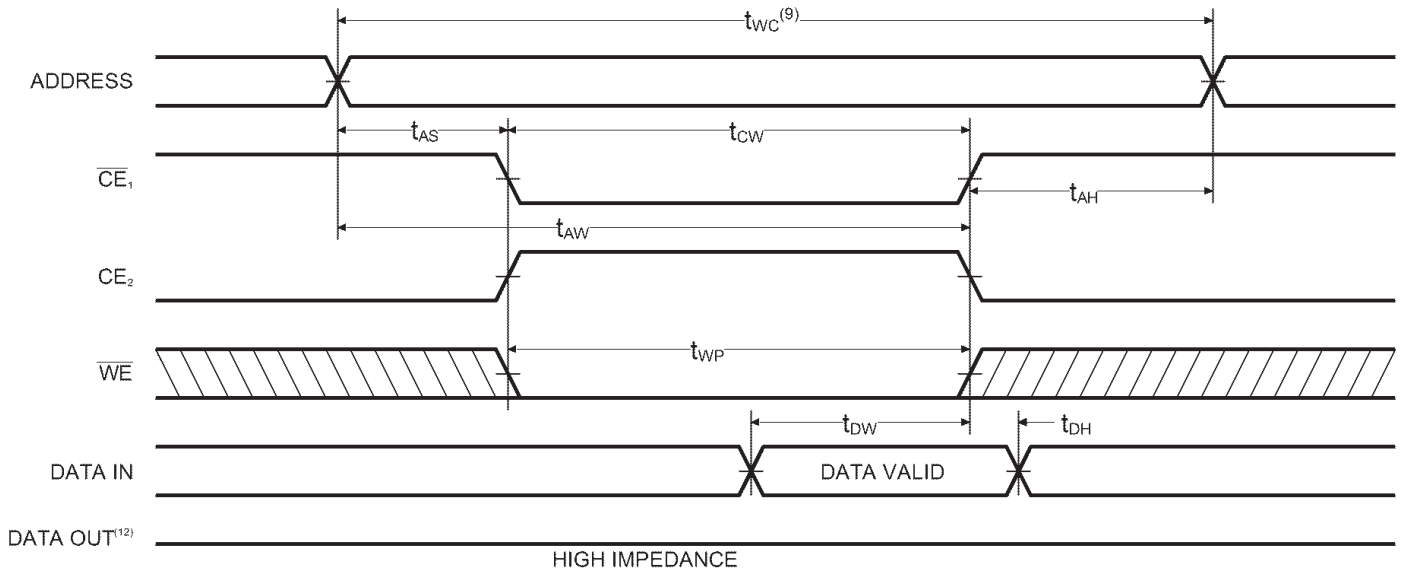


#### Notes:

6.  $\overline{CE}_1$  and  $\overline{WE}$  are LOW and  $CE_2$  is HIGH for WRITE cycle.
7.  $\overline{OE}$  is LOW for this WRITE cycle to show  $t_{WZ}$  and  $t_{OW}$ .
8. If  $\overline{CE}_1$  goes HIGH or  $CE_2$  goes LOW simultaneously with  $\overline{WE}$  HIGH, the output remains in a high impedance state.
9. Write Cycle Time is measured from the last valid address to the first transitioning address.



### TIMING WAVEFORM OF WRITE CYCLE NO.2 ( $\overline{CE}$ CONTROLLED)<sup>(6)</sup>



### AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	3ns
Input Timing Reference Level	1.5V
Output Timing Reference Level	1.5V
Output Load	See Fig. 1 and 2

### TRUTH TABLE

Mode	$\overline{CE}_1$	$CE_2$	$\overline{OE}$	$\overline{WE}$	I/O	Power
Standby	H	X	X	X	High Z	Standby
Standby	X	L	X	X	High Z	Standby
$D_{OUT}$ Disabled	L	H	H	H	High Z	Active
Read	L	H	L	H	$D_{OUT}$	Active
Write	L	H	X	L	$D_{IN}$	Active

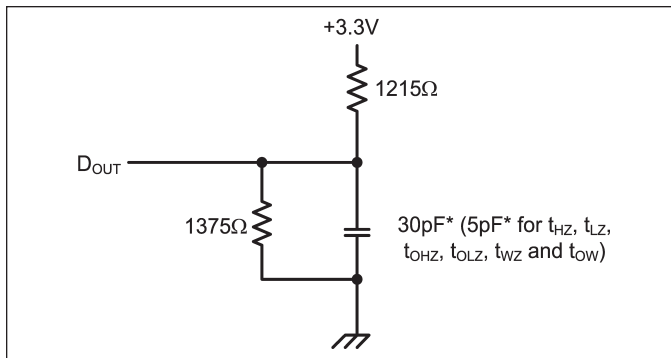


Figure 1. Output Load

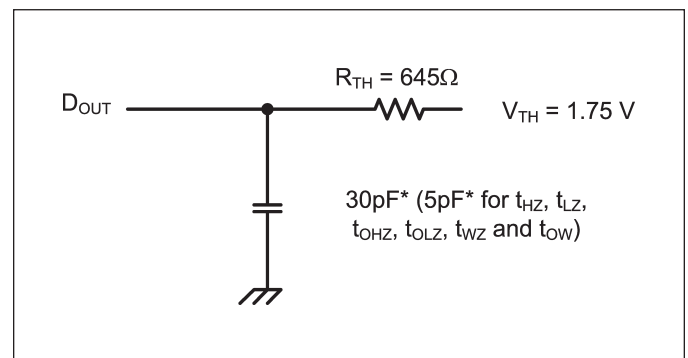


Figure 2. Thevenin Equivalent

\* including scope and test fixture.

**Note:**

Because of the high speed of the P3C1024L, care must be taken when testing this device; an inadequate setup can cause a normal functioning part to be rejected as faulty. Long high-inductance leads that cause supply bounce must be avoided by bringing the  $V_{CC}$  and ground planes directly up to the contactor fingers. A 0.01  $\mu$ F high frequency capacitor is also required between  $V_{CC}$  and ground.

To avoid signal reflections, proper termination must be used; for example, a 50 $\Omega$  test environment should be terminated into a 50 $\Omega$  load with 1.75V (Thevenin Voltage) at the comparator input, and a 595 $\Omega$  resistor must be used in series with  $D_{OUT}$  to match 645 $\Omega$  (Thevenin Resistance).

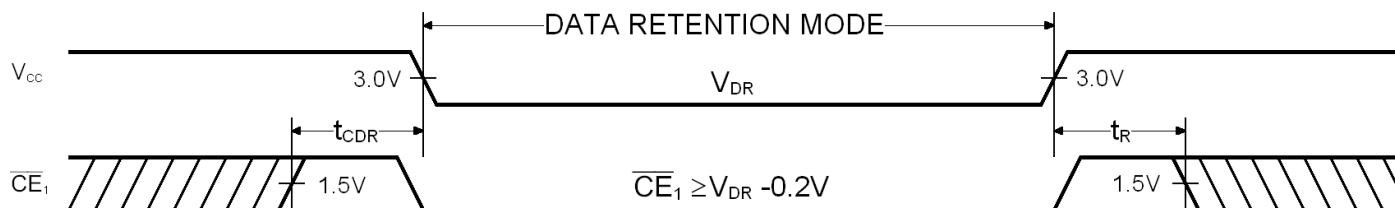


## DATA RETENTION

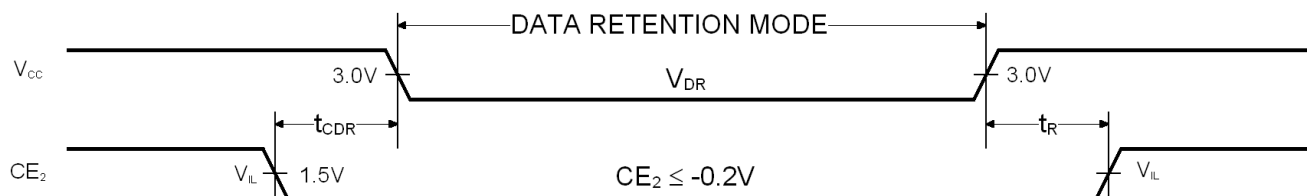
Symbol	Parameter	Test Conditions	Min	Max	Unit
$V_{DR}$	$V_{CC}$ for Data Retention	$\overline{CE}_1 \geq V_{CC} - 0.2V$ , $CE_2 \leq 0.2V$ , $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	2.0		V
$I_{CCDR}^{(1)}$	Data Retention Current	$V_{DR} = 2.0V$		10	$\mu A$
$t_{CDR}$	Chip Deselect to Data Retention Time	See Retention Waveform	0		ns
$t_R$	Operating Recovery Time <sup>(2)</sup>		100		$\mu A$

1.  $\overline{CE}_1 \geq V_{DR} - 0.2V$ ,  $CE_2 \geq V_{DR} - 0.2V$  or  $CE_2 \leq 0.2V$ ; or  $\overline{CE}_1 \leq 0.2V$ ,  $CE_2 \geq 0.2V$ ;  $V_{IN} \geq V_{DR} - 0.2V$  or  $V_{IN} \leq 0.2V$

### LOW $V_{CC}$ DATA RETENTION WAVEFORM 1 ( $\overline{CE}_1$ CONTROLLED)

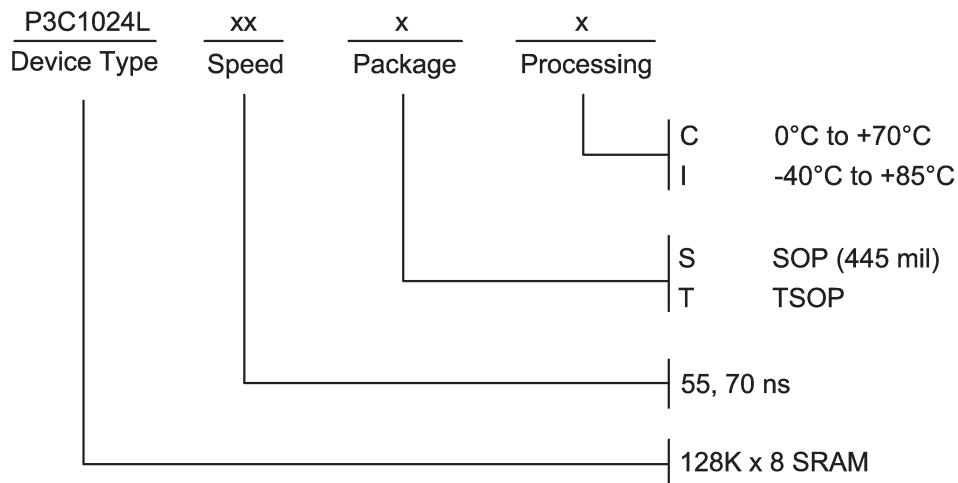


### LOW $V_{CC}$ DATA RETENTION WAVEFORM 2 ( $CE_2$ CONTROLLED)





### ORDERING INFORMATION



### SELECTION GUIDE

The P3C1024L is available in the following temperature, speed and package options.

Temperature Range	Package	Speed	
		-55	-70
Commercial	Plastic SOP (445 mil)	-55SC	-70SC
	TSOP	-55TC	-70TC
Industrial	Plastic SOP (445 mil)	-55SI	-70SI
	TSOP	-55TI	-70TI

### TSOP PIN CONFIGURATION

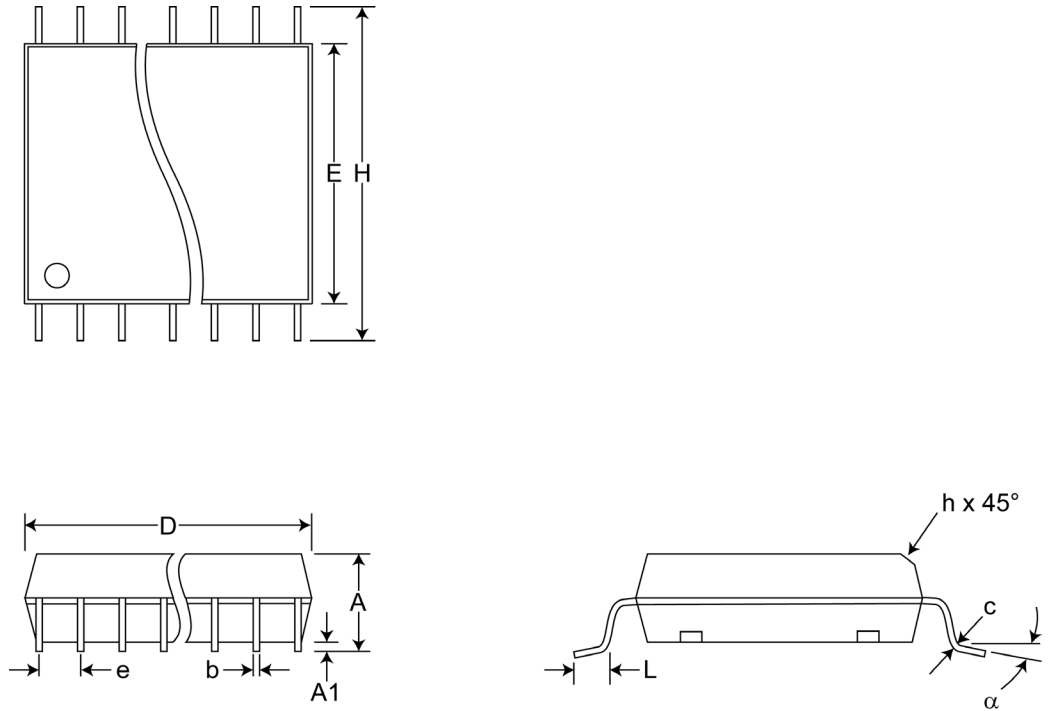






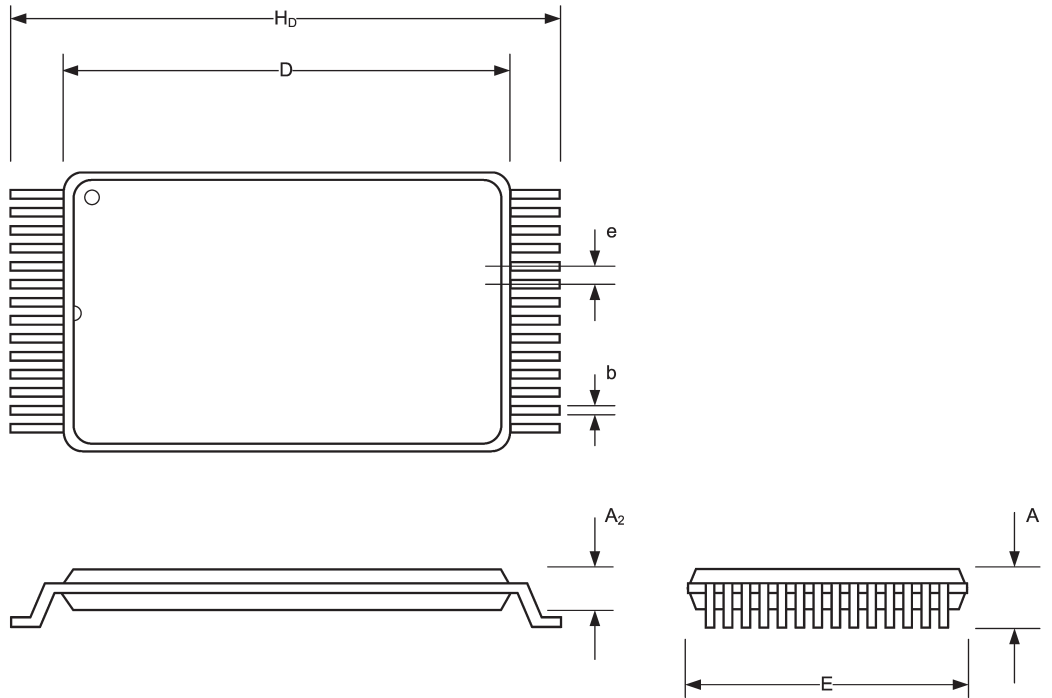
Pkg #	S12	
# Pins	32 (445 Mil)	
Symbol	Min	Max
A	-	0.118
A1	0.004	-
A2	0.101	0.111
b	0.014	0.020
C	0.006	0.012
D	0.793	0.817
e	0.050 BSC	
E	0.440	0.450
H	0.546	0.566
L	0.023	0.039
L1	0.047	0.063
$\alpha$	0°	4°

**SOIC/SOP SMALL OUTLINE IC PACKAGE**



Pkg #	T3	
# Pins	32	
Symbol	Min	Max
A	-	0.048
A <sub>2</sub>	0.037	0.042
b	0.006	0.011
D	0.720	0.729
E	0.307	0.323
e	0.50 mm BSC	
H <sub>b</sub>	0.779	0.796

**TSOP THIN SMALL OUTLINE PACKAGE (8 x 20 mm)**





## REVISIONS

<b>DOCUMENT NUMBER</b>	SRAM 132
<b>DOCUMENT TITLE</b>	P3C1024L ULTRA LOW POWER 128K x 8 CMOS STATIC RAM

<b>REV</b>	<b>ISSUE DATE</b>	<b>ORIGINATOR</b>	<b>DESCRIPTION OF CHANGE</b>
OR	April 2006	JDB	New Data Sheet
A	Feb 2009	JDB	Updated SOIC/SOP package drawing, new datasheet format